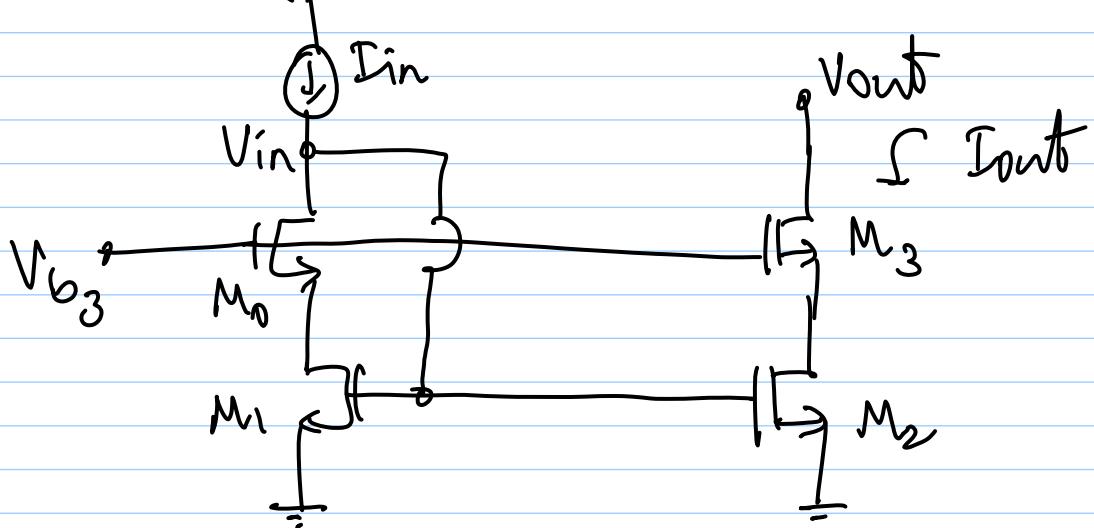


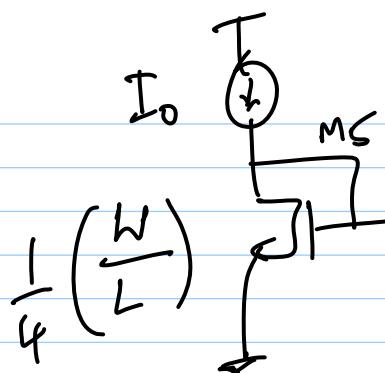
(2/1/1<sup>2</sup>)

Lec 6



How to generate V<sub>b3</sub>?

i)

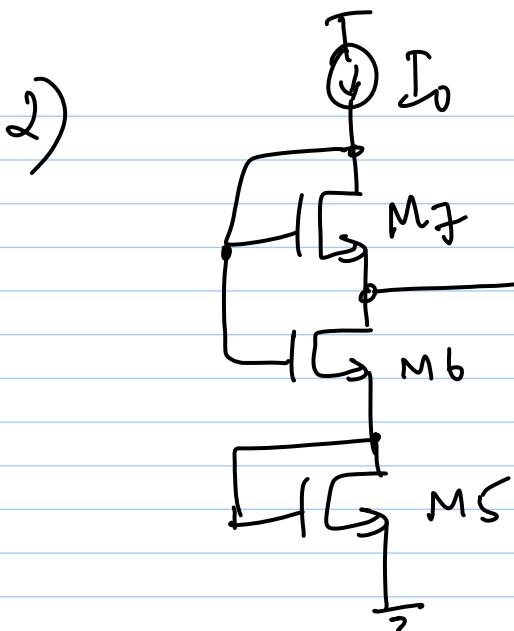


$$V_{b3} = V_{T5} + 2V_{DSAT}$$

$\rightarrow V_{T5} < V_{T3}$  due to body effect

$$\Rightarrow V_{DS2} < V_{DSAT}$$

$\therefore$  some margin is required



\*  $M_7$  has very large  $W/L$   
 $\Rightarrow V_{AS7} \approx V_{T7}$   
 $V_{b3} = V_{AS5} + V_{DS6}$   
 $= V_{AS5} + V_{US6} - V_{T7}$   
 $\approx V_{T5} + 2V_{DSAT}$

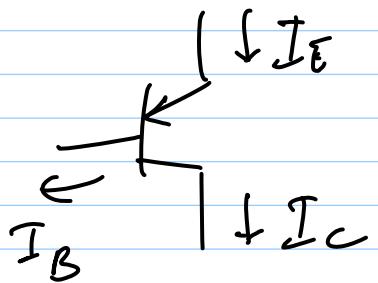
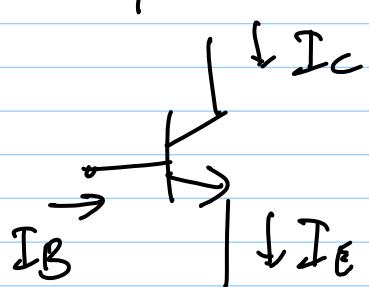
however, note that  $V_{T7} \neq V_{T6}$

\* For more types, see

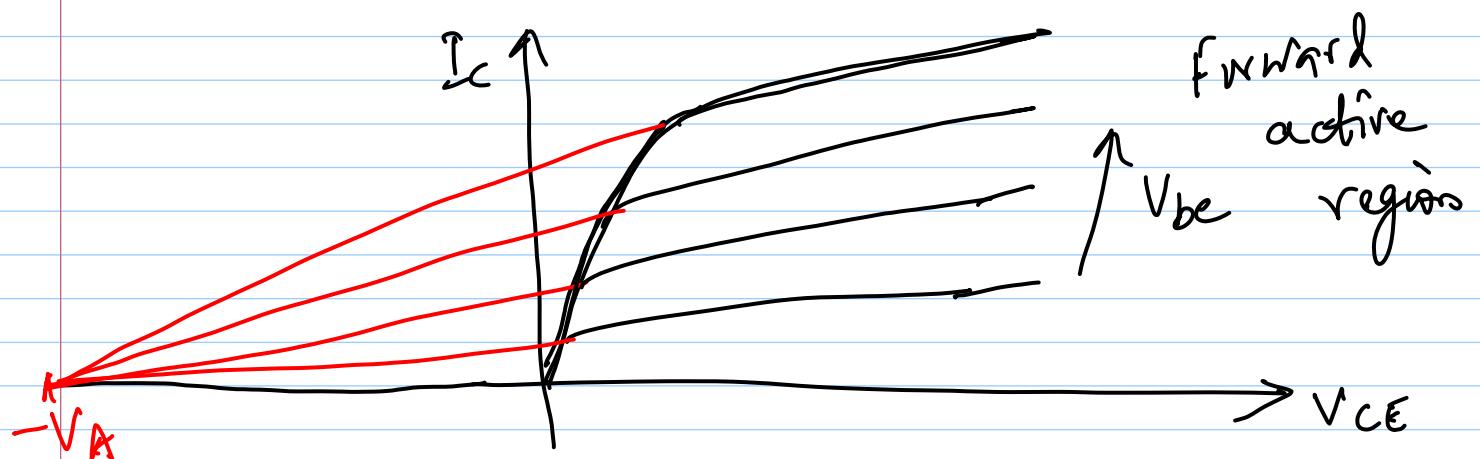
Razavi - figs 5.14 & 5.15

Gray & Meyer - figs 4.11, 4.12 & 4.13

## Bipolar Devices



$$I_E = I_B + I_C$$



$$I_C = I_s e^{\frac{V_{BE}}{N\tau}} \left( 1 + \frac{V_{CE}}{V_A} \right)$$

$-V_A$  = early voltage

$$V_T = \frac{kT}{q} \approx 26mV$$

\* due to base width modulation

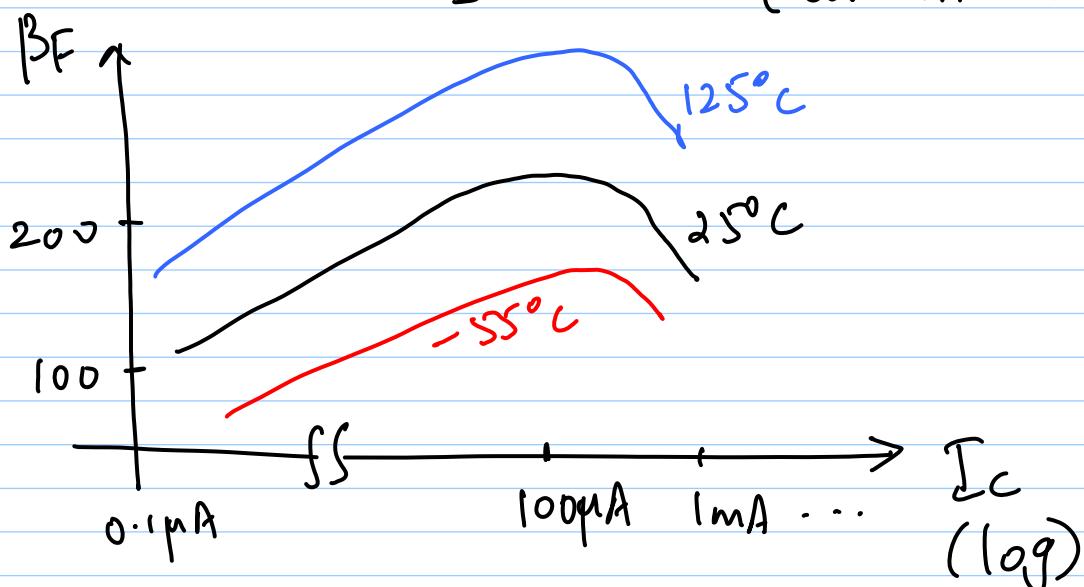
$$1) r_o = \frac{\partial I_C}{\partial V_{CE}} ; \quad V_A = \frac{I_C}{\frac{\partial I_C}{\partial V_{CE}}}$$

$$\Rightarrow r_o \approx \frac{V_A}{I_C}$$

$V_A$  is independent of  $I_C$  etc. & is a fixed process parameter

$$2) g_m = \frac{\partial I_C}{\partial V_{be}} = \frac{I_C}{V_T}$$

$$\beta_F = \frac{I_C}{I_B} \quad \leftarrow \text{function of } I_C \text{ (current density)}$$



$$I_B = I_C / \beta_F \Rightarrow \Delta I_B = \frac{d}{dI_C} \left( \frac{I_C}{\beta_F} \right) \cdot \Delta I_C$$

$$\Rightarrow \beta_0 = \frac{\Delta I_C}{\Delta I_B} = \frac{i_C}{i_B} = \left[ \frac{d}{dI_C} \left( \frac{I_C}{\beta_F} \right) \right]^{-1}$$

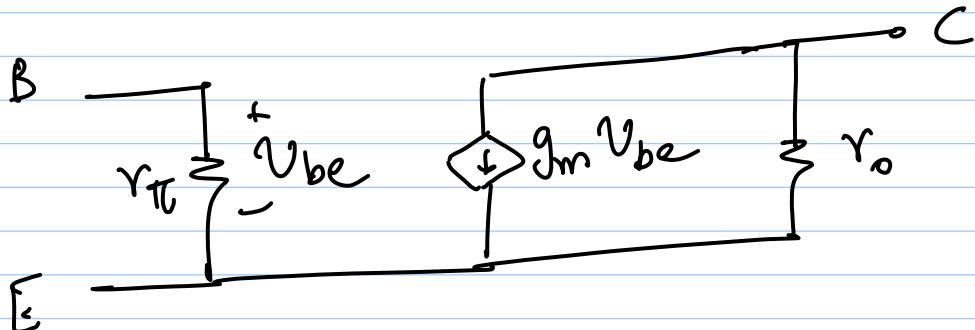
↑  
small-signal  
current gain

$\beta_0 \neq \beta_F$  in general

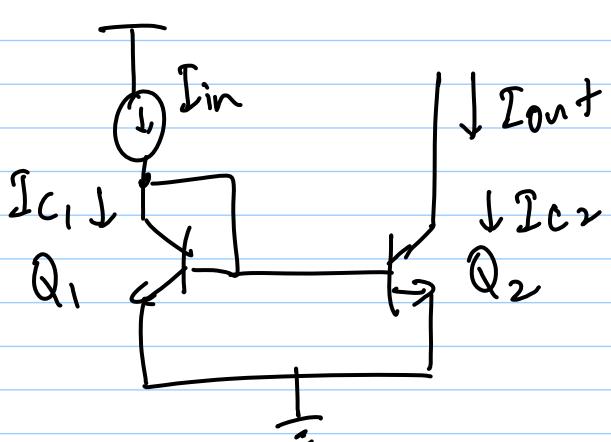
3) Input res.  $r_{\pi} = \left( \frac{\Delta I_B}{\Delta V_{be}} \right)^{-1}$  Q-pt.

$$r_{\pi} = \frac{\beta_0}{g_m}$$

low-freq model:



Bipolar CMOS  
Simple CM:



$$I_{C_2} = I_{out}$$

$$V_{be_1} = V_{ber}$$

$$V_T \ln \frac{I_{C_1}}{I_{S_1}} = V_T \ln \frac{I_{C_2}}{I_{S_2}}$$

$$\Rightarrow \frac{\underline{I_{C_2}}}{\underline{I_{C_1}}} = \frac{\underline{I_{S_2}}}{\underline{I_{S_1}}}$$

$$I_S \propto A_{EB}$$

← EB inj. Area  
— design parameter

assume identical transistors

$$I_{S_1} = I_{S_2} \Rightarrow I_{C_1} = I_{C_2} = I_{out}$$

$$I_{in} = I_{C_1} + I_{b_1} + I_{b_2}$$

$$= I_{C_1} + \frac{I_{C_1}}{\beta_F} + \frac{I_{C_2}}{\beta_F}$$

$$= I_{out} \left[ 1 + \frac{2}{\beta_F} \right]$$

$$I_{out} = \frac{I_{in}}{1 + \frac{2}{\beta_F}}$$

← gain error due to finite  $\beta_F$

If you have  $n$  mirror legs,

$$I_{out} = \frac{I_{in}}{1 + \frac{(n+1)}{\beta_F}}$$

If  $Q_1 \neq Q_2$ ,  $I_{S1} \neq I_{S2}$

$$\Rightarrow I_{in} = I_{C1} \left( 1 + \frac{1}{\beta_F} \right) + \frac{I_{C2}}{\beta_F}$$

$$= I_{out} \left[ \frac{1}{\beta_F} + \frac{I_{S1}}{I_{S2}} \left( 1 + \frac{1}{\beta_F} \right) \right]$$

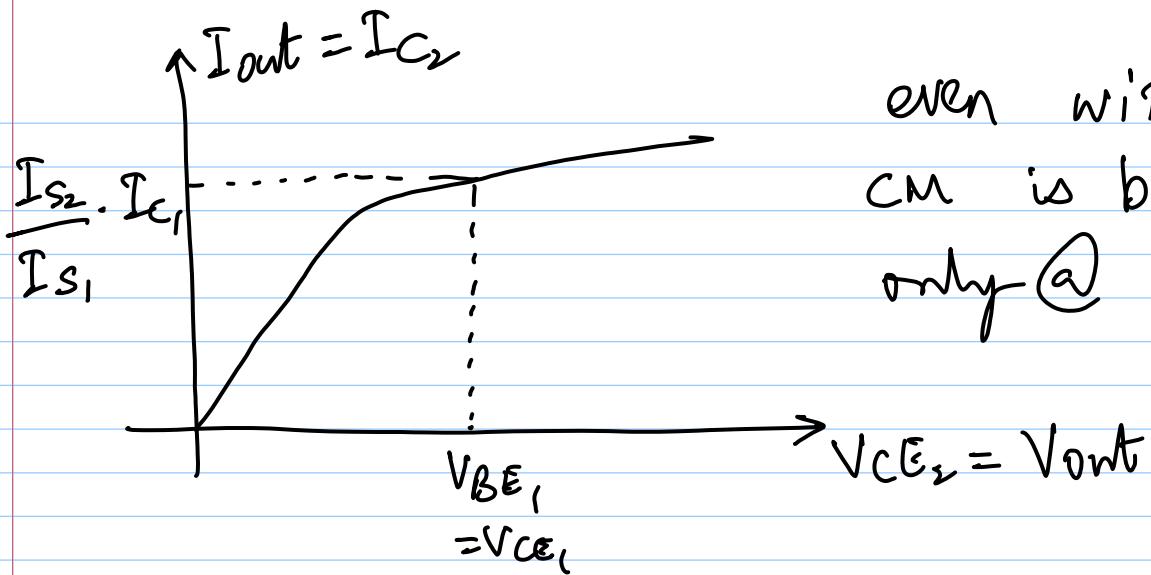
$$I_{out} = \frac{\left( \frac{I_{S2}}{I_{S1}} \right) I_{in}}{1 + \frac{\left( 1 + \frac{I_{S2}}{I_{S1}} \right)}{\beta_F}}$$

Output impedance errors:

$$I_{C1} = I_{S1} e^{\frac{V_{BE1}}{V_T}} \left( 1 + \frac{V_{CE1}}{V_A1} \right)$$

$$I_{C2} = I_{S2} e^{\frac{V_{BE2}}{V_T}} \left( 1 + \frac{V_{CE2}}{V_A2} \right)$$

$$\Rightarrow I_{out} = \frac{\left( \frac{I_{S2}}{I_{S1}} \right) \cdot I_{in}}{1 + \frac{\left( 1 + \frac{I_{S2}}{I_{S1}} \right)}{\beta_F}} \cdot \left[ 1 + \frac{V_{CE2} - V_{CE1}}{V_A} \right]$$



even with  $\beta_F = \infty$ ,  
CM is balanced  
only @ 1 pt.

Error term

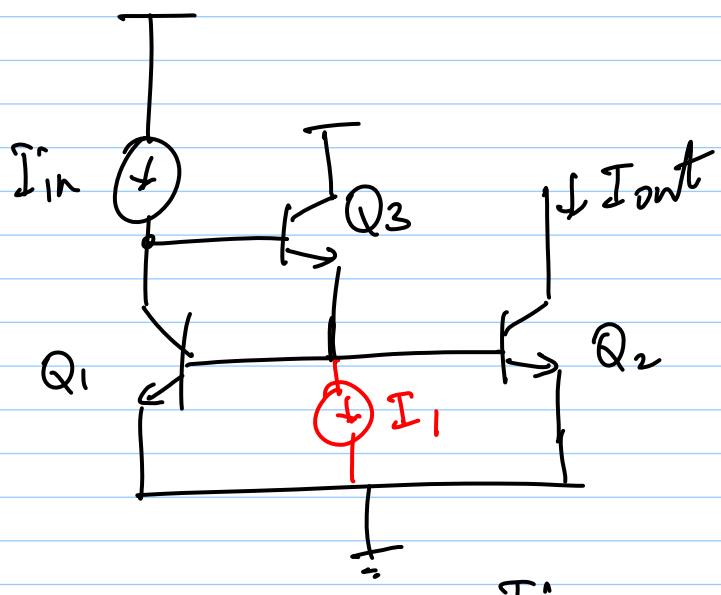
$$E = \frac{1 - \left( \frac{V_{CE_2} - V_{CE_1}}{V_A} \right)}{1 + \frac{1 + \frac{I_{S2}/I_{S1}}{\beta_F}}{1 + \frac{I_{S2}/I_{S1}}{\beta_F}}} \approx \frac{V_{CE_2} - V_{CE_1}}{V_A} - \frac{1 + \frac{I_{S2}/I_{S1}}{\beta_F}}{1 + \frac{I_{S2}/I_{S1}}{\beta_F}}$$

$$V_{out\min.} = V_{CE_{SAT_2}} \approx 0.2V$$

$$R_{in} = \frac{1}{\frac{1}{g_m} \left( 1 + \frac{1}{\beta_0} \right) + \frac{1}{r_o}} \approx \frac{1}{g_m}$$

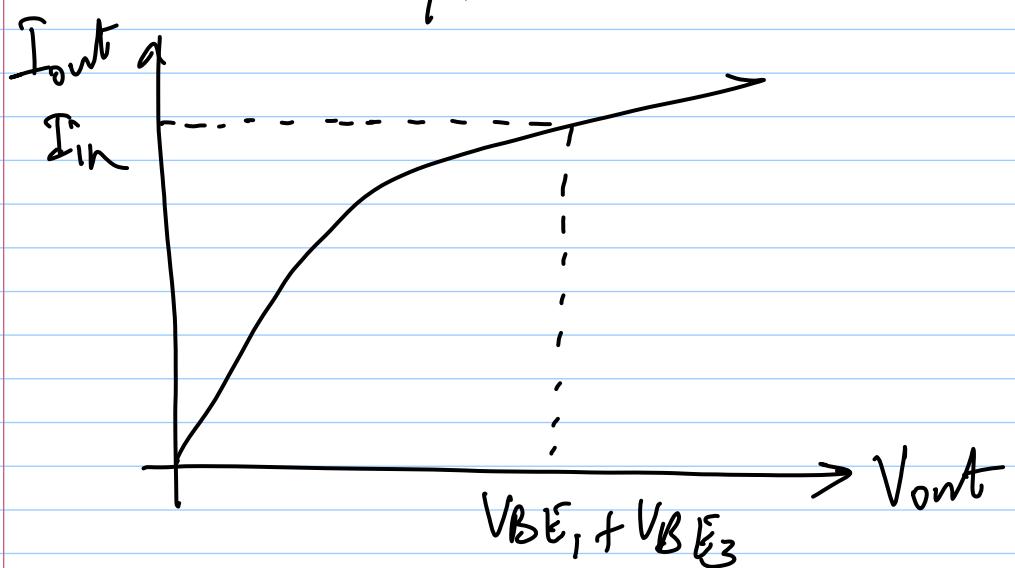
$$R_{out} = r_o$$

## Simple CM with β-helpers



$$I_{out} = \frac{I_{in}}{1 + \frac{2}{\beta_F(\beta_F + 1)}} \approx I_{in} \left[ 1 - \frac{2}{\beta_F(\beta_F + 1)} \right]$$

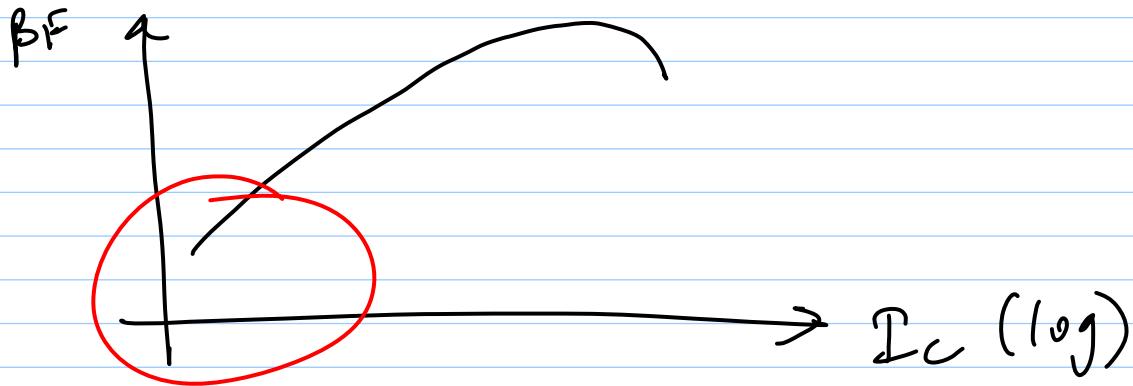
$$\epsilon \propto \frac{1}{\beta_F^2}$$



↑  $V_{in DC}$  is different  
(different balance point)

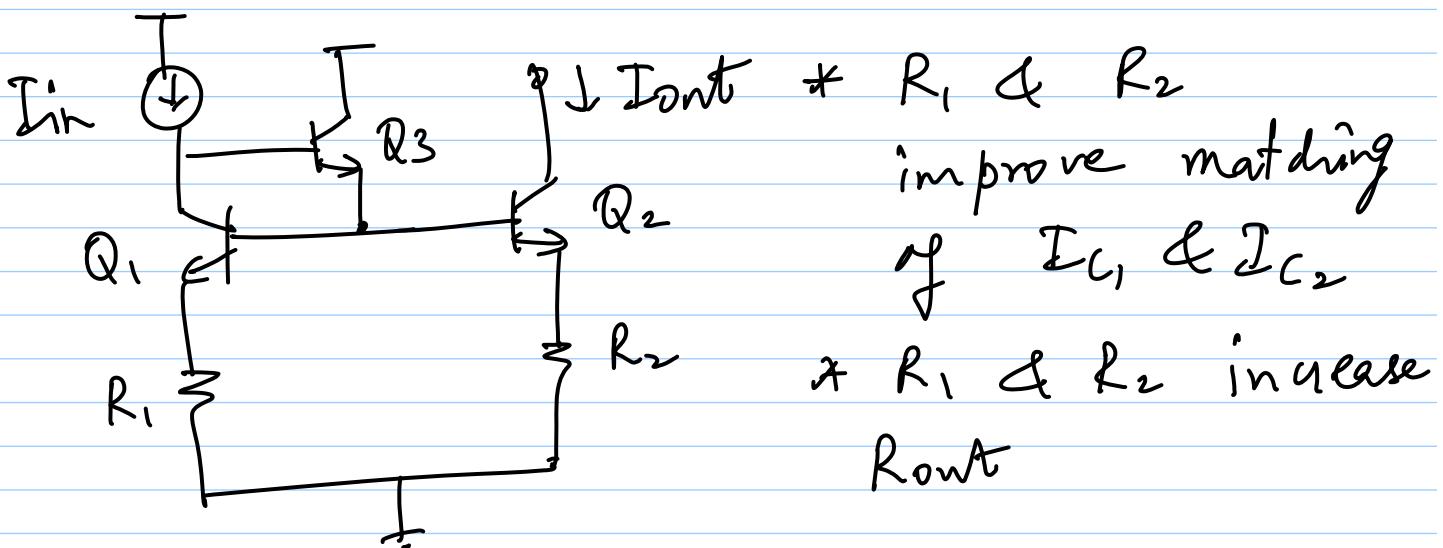
$\beta_{F3}$  could be very small

$$I_{E3} = I_{b1} + I_{b2} \leftarrow \text{very small}$$



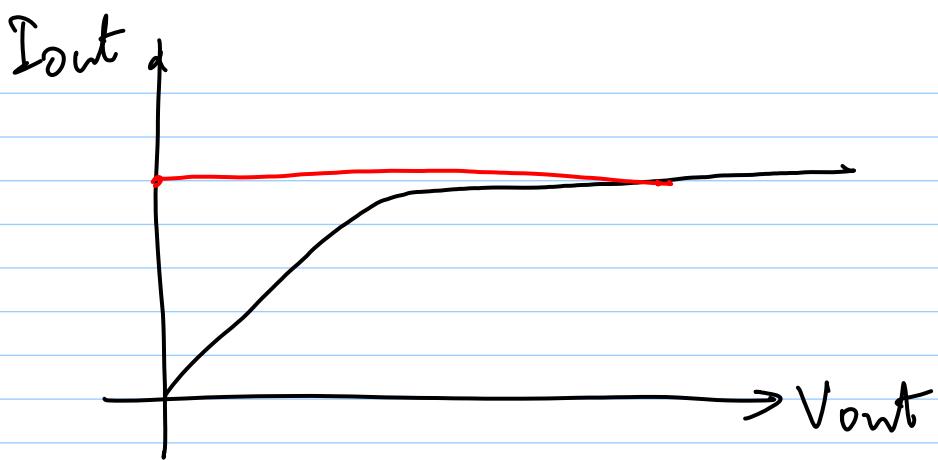
$\Rightarrow$  add c.s. to increase  $I_{E3}$

BJT CM w/ Emitter degen.:



$$R_{out} \approx r_{o2} (1 + g_{m2} R_2)$$

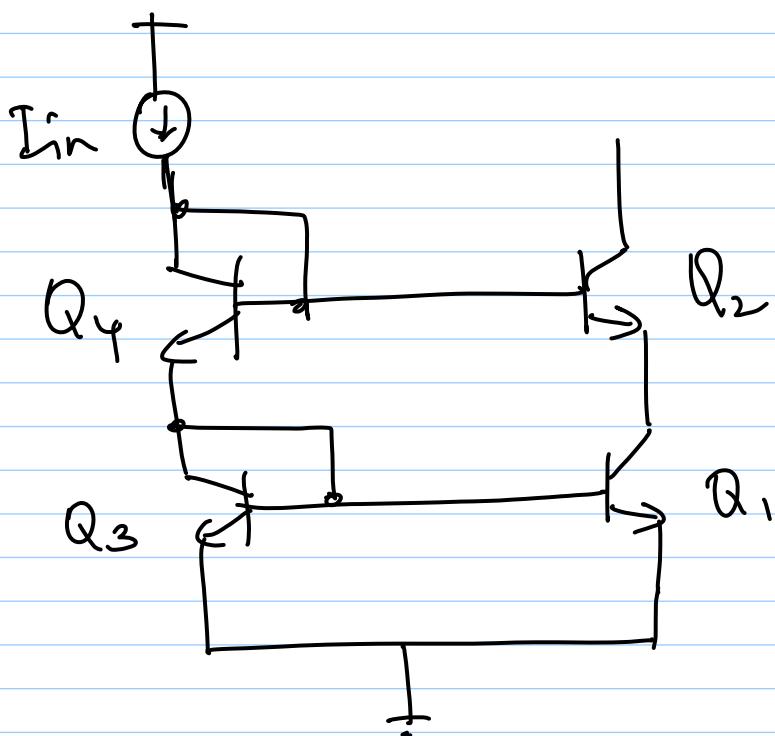
ε reduces (H.W.)



$$V_{in} = I_{in} R_1 + V_{BE1} + V_{BE3}$$

$$V_{out \min.} = I_{out} R_2 + V_{CESAT_2}$$

### BJT cascode



$$V_{in} = V_{BE3} + V_{BE4}$$

$$V_{CE1} = V_{BE3} + V_{BE4}$$

$$- V_{BE2}$$

$$\approx V_{BE3}$$

$$V_{out \ min.} = V_{BE3} + V_{CESAT_2}$$

$\sim 900mV$

$$R_{out} \approx \frac{\beta_0 R_2}{2}$$

high  $R_{out} \leftrightarrow V_{out \ min.}$  tradeoff

Other types:

→ Wilson & Balanced Wilson C.M.

→ Widlar C.S.

→ Bipolar peaking C.S.